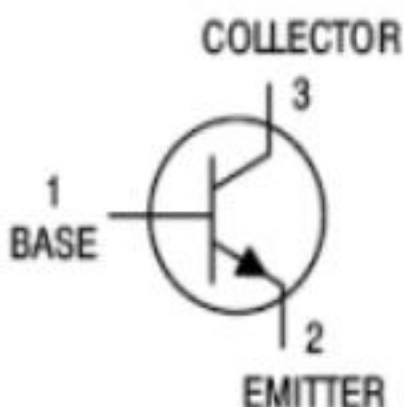


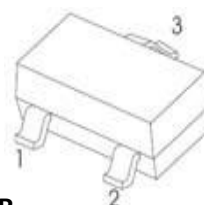
2SD596 TRANSISTOR (NPN)

Equivalent Circuit:



SOT-23

1.BASE
2.EMITTER
3.COLLECTOR



FEATURES:

- ※ Complimentary to 2SB624
- ※ High DC Current gain

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	VCBO	30	V
Collector-Emitter Voltage	VCEO	25	V
Emitter-Base Voltage	VEBO	5	V
Collector Current	IC	700	mA
Collector Power Dissipation	PC	200	mW
Thermal Resistance From Junction To Ambient	RθJA	625	°C/W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55~+150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

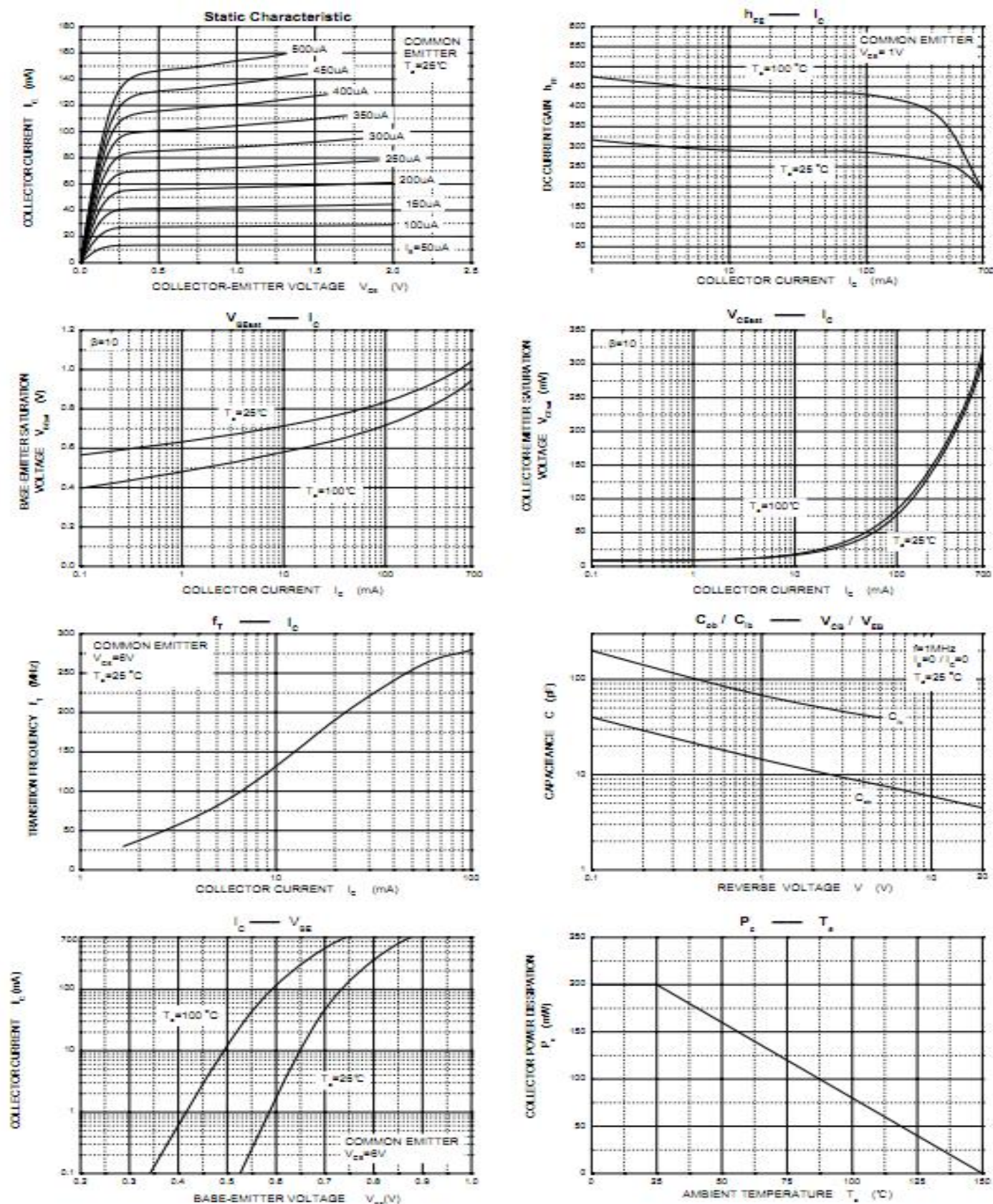
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC= 100μA, IE=0	30			V
Collector-emitter breakdown voltage	V(BR)CEO	IC= 1mA, IB=0	25			V
Emitter-base breakdown voltage	V(BR)EBO	IE=100μA, IC=0	5			V
Collector cut-off current	ICBO	VCB=30 V , IE=0			0.1	μA
Emitter cut-off current	IEBO	VEB= 5V , IC=0			0.1	μA
DC current gain	hFE	VCE=1V, IC= 100mA	100		400	
	hFE	VCE=1V, IC= 700mA	50			
Collector-emitter saturation voltage	VCE(sat)	IC=700 mA, IB= 70mA			0.6	V
Base-emitter saturation voltage	VBE(sat)	VCE=6V, IC= 10mA			0.7	V
Transition frequency	fT	VCE=2V, IC= 10mA f=100MHz	170			MHz
Collector Output Capacitance	Cob	VCE=10V, IE= 0 f=1MHz		12		pf

※ Pulse test: Pulse width≤350μs,Duty Cycle≤2%

CLASSIFICATION OF hFE

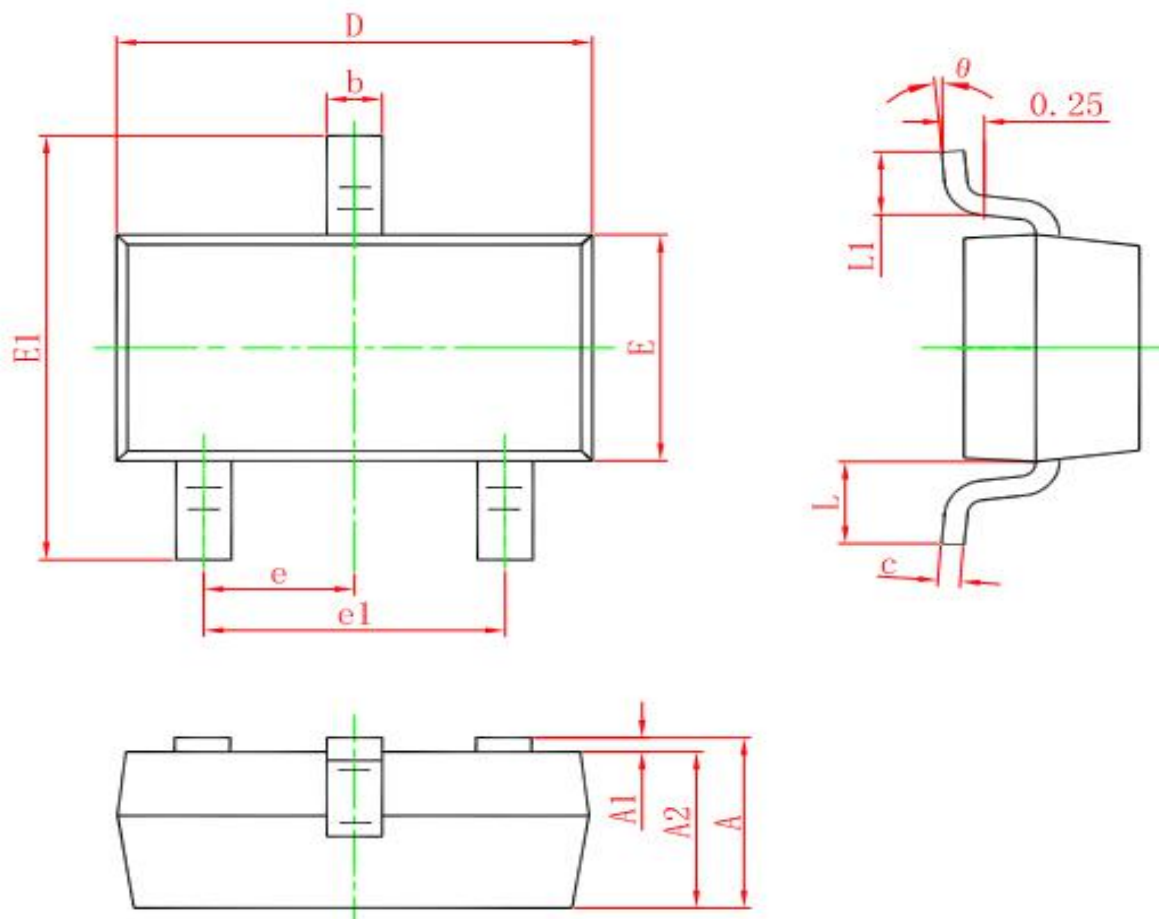
MARKING	DV1	DV2	DV3	DV4	DV5
Range	110-180	135-220	170-270	200-320	250-400

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS





SOT-23 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°